



Docket: 740756-1914

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Shunpei YAMAZAKI et al.)
Serial No. 09/235,770) Art Unit: 2813
Filed: January 25, 1999) Examiner: L. Schillinger
For: SEMICONDUCTOR DEVICE AND)
METHOD FOR FORMING THE)
SAME) Date: March 13, 2002

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TC 2800 MAIL ROOM

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents and Trademarks

Washington, D.C. 20231


Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

Copies of these references are submitted herewith in accordance with 37 C.F.R. 1.98(a).

It is noted that these references were recently received in a Japanese counterpart application. JP 4-192466 teaches the use of silicon nitride or aluminum nitride as an insulator layer having an excellent thermal conductivity.

Respectfully submitted,


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